



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

WBFBP-03B Plastic-Encapsulate Transistors

TP9013NND03 TRANSISTOR

DESCRIPTION

NPN Epitaxial Silicon Transistor

FEATURES

High Collector Current. ($I_C=500\text{mA}$)

Complementary to TP9012NND03

Excellent h_{FE} linearity.

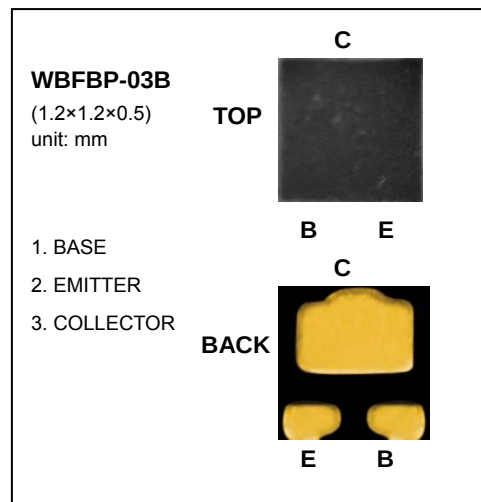
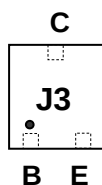
APPLICATION

150mW Output Amplifier of Potable Radios in Class

B Push-pull Operation.

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM,Note book PC, etc.)

MARKING: J3



MAXIMUM RATINGS $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Dissipation	150	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20\text{V}, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}, I_C=50\text{mA}$	120		400	
	h_{FE2}	$V_{CE}=1\text{V}, I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=20\text{mA}, f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=6\text{V}, I_E=0, f=1\text{MHz}$			8	pF

CLASSIFICATION OF h_{FE1}

Rank	L	H	J
Range	120-200	200-350	300-400

Typical Characteristics

TP9013NND03

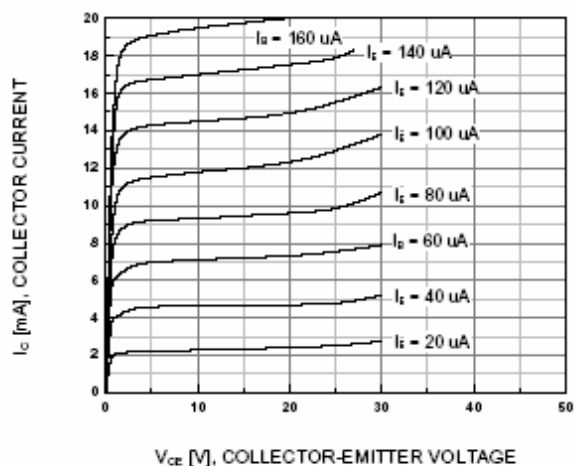


Figure 1. Static Characteristic

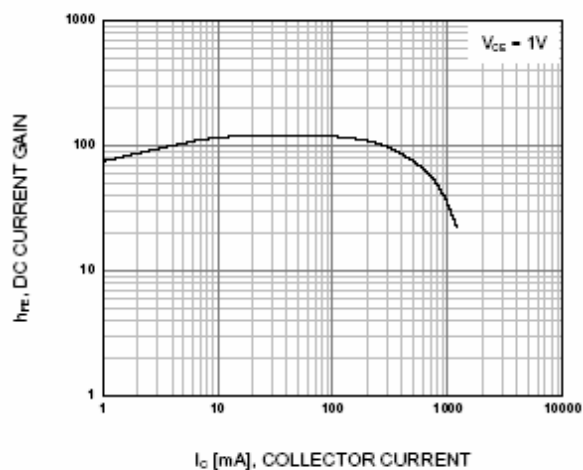


Figure 2. DC current Gain

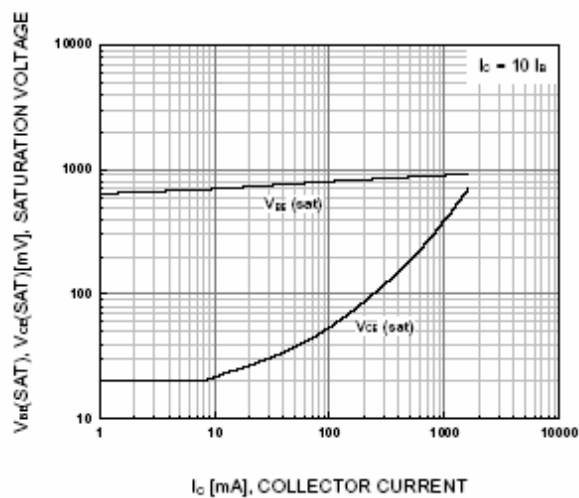


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

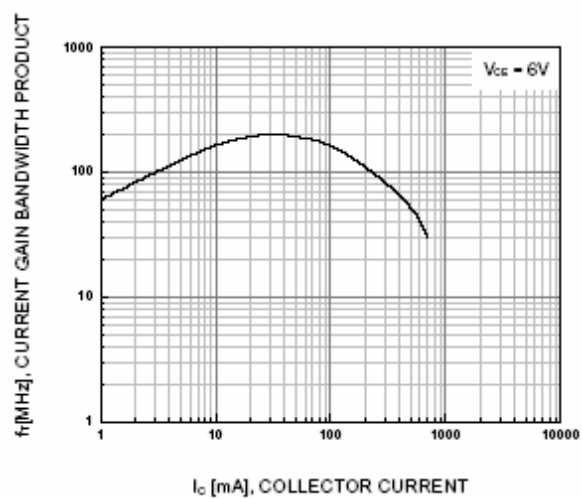


Figure 4. Current Gain Bandwidth Product